Amendments to the Claims:

Claims 1-7 (Cancelled)

8. (New) A method of manufacturing a thin film transistor using a chemical vapor deposition (CVD) apparatus having a frequency power supply, an electrode, and a gas inlet, the method comprising:

placing a substrate on the electrode of the CVD apparatus; and

applying electric power having a frequency from the frequency power supply to the electrode, while providing a reaction gas to the substrate via the gas inlet to form an insulator layer on the substrate, the reaction gas having a mixture gas of monosilane and nitrous oxide.

9. (New) The method of claim 8, wherein the reaction gas includes a mixture gas of monosilane and nitrous oxide having a flow ratio of between 10% and 50%.

10. (New) The method of claim 8, wherein a ratio of nitrous oxide to monosilane is at least 10.

11. (New) The method of claim 8, wherein the reaction gas includes gas selected from helium, hydrogen, xenon, oxygen, argon, nitrogen and a mixture thereof.

12. (New) The method of claim 8, wherein the insulator layer includes a gate insulator.

13. (New) The method of claim 8, wherein the insulator layer includes an interspacing insulator.

14. (New) The method of claim 8, wherein the insulator layer includes a silicon oxide layer.

15. (New) The method of claim 8, wherein the frequency is between 13.56 MHz and 100 MHz.

16. (New) The method of claim 8, wherein the frequency is about 40.68 MHz.

17. (New) The method of claim 8, wherein the frequency is about 27.12 MHZ.